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## NTE553 Schottky Barrier Diode

**Description:**

The NTE553 is a silicon schottky barrier diode in a DO35 style package for use in UHF and VHF switching applications.

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Reverse Voltage, $V_R$ .....	-35V
Forward Current, $I_F$ .....	100mA
Power Dissipation, $P_D$ .....	150mW
Operating Temperature Range, $T_{opr}$ .....	-20° to + 60°C
Storage Temperature range, $T_{stg}$ .....	-45° to + 125°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = -10\mu\text{A}$	-35	-	-	V
Reverse Leakage Current	$I_R$	$V_R = -25\text{V}$	-	-	-0.1	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 10\text{mA}$	-	-	1.0	V
Diode Capacitance	$C_T$	$V_R = -6\text{V}, f = 1\text{MHz}$	-	-	1.2	pf
Series Resistance	$R_S$	$I_F = 2\text{mA}, f = 100\text{MHz}$	-	-	1.2	$\Omega$
Series Inductance	$L_S$	$f = 250\text{MHz}$	-	3	-	nH

